

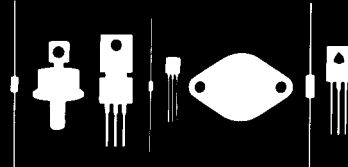
CENTRAL SEMICONDUCTOR CORP.

Central Semiconductor Corp.

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145 Adams Avenue
Hauppauge, New York 11788



D33D26

NPN SILICON TRANSISTOR

JEDEC TO-92 CASE (ECB)

DESCRIPTION

The CENTRAL SEMICONDUCTOR D33D26 type is an NPN silicon transistor manufactured by the epitaxial planar process, designed for general purpose, high current applications.

MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$)

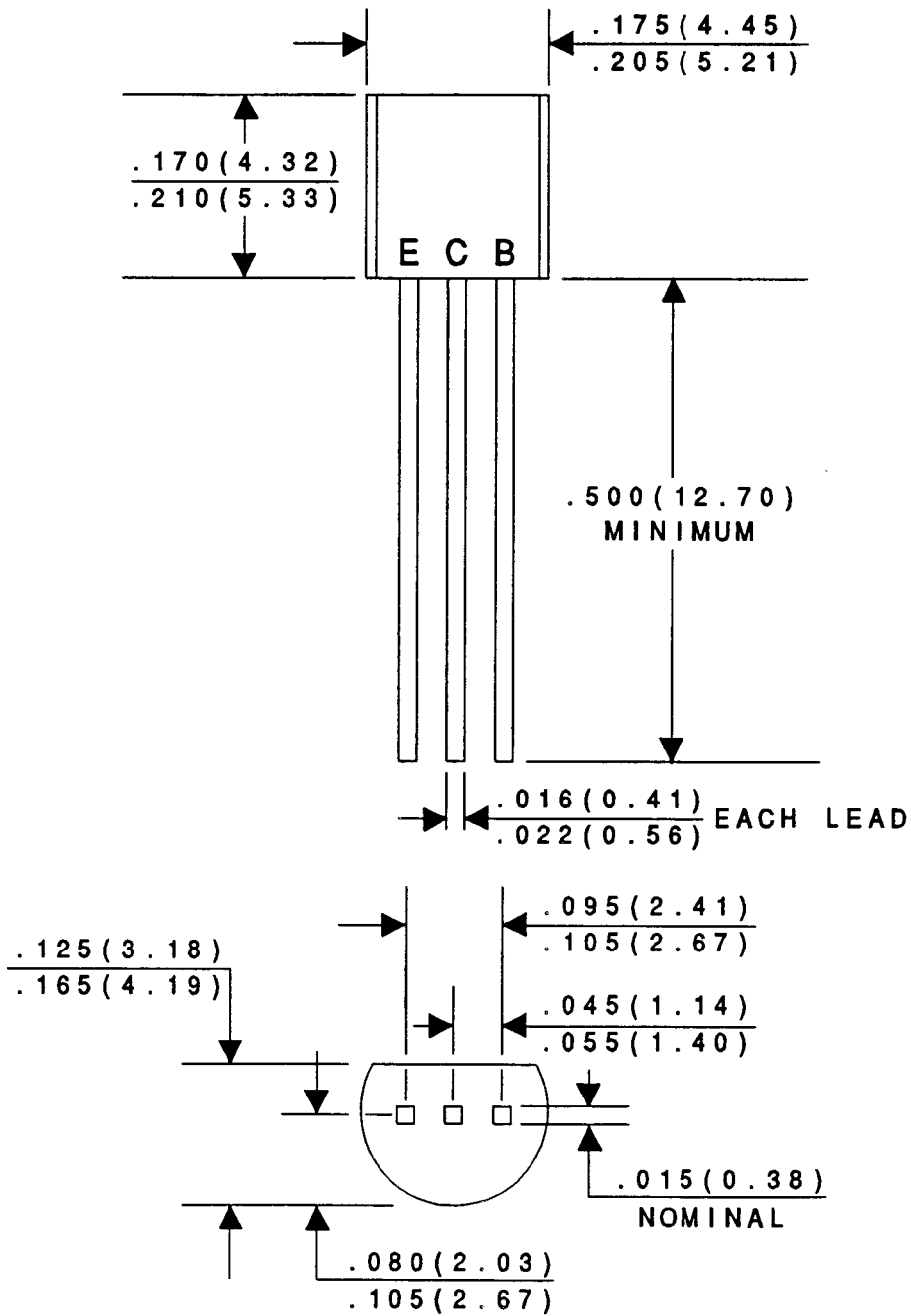
	<u>SYMBOL</u>		<u>UNITS</u>
Collector-Base Voltage	V_{CBO}	50	V
Collector-Emitter Voltage	V_{CES}	50	V
Collector-Emitter Voltage	V_{CEO}	40	V
Emitter-Base Voltage	V_{EBO}	5.0	V
Continuous Collector Current	I_C	750	mA
Peak Collector Current	I_{CM}	1000	mA
Power Dissipation	P_D	625	mW
Operating and Storage			
Junction Temperature	T_J, T_{stg}	-65 to +150	$^\circ\text{C}$
Thermal Resistance	θ_{JA}	200	$^\circ\text{C}/\text{W}$

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

<u>SYMBOL</u>	<u>TEST CONDITIONS</u>	<u>MIN</u>	<u>MAX</u>	<u>UNITS</u>
I_{CES}	$V_{CE} = 25\text{V}$		100	nA
I_{CES}	$V_{CE} = 25\text{V}, T_A = 100^\circ\text{C}$		15	μA
BV_{CES}	$I_C = 10\mu\text{A}$	50		V
BV_{CEO}	$I_C = 10\text{mA}$	40		V
BV_{EBO}	$I_E = 10\mu\text{A}$	5.0		V
$V_{CE(SAT)}$	$I_C = 500\text{mA}, I_B = 50\text{mA}$		0.75	V
$V_{BE(SAT)}$	$I_C = 500\text{mA}, I_B = 50\text{mA}$		1.2	V
h_{FE}	$V_{CE} = 2.0\text{V}, I_C = 2.0\text{mA}$	150	300	
h_{FE}	$V_{CE} = 2.0\text{V}, I_C = 500\text{mA}$	25		
C_{cb}	$V_{CB} = 10\text{V}, f = 1.0\text{MHz}$		15	pF
C_{eb}	$V_{EB} = 0.5\text{V}, f = 1.0\text{MHz}$		55	pF
f_T	$V_{CE} = 2.0\text{V}, I_C = 50\text{mA}, f = 20\text{MHz}$	135		MHz

(OVER)

JEDEC TO-92 - MECHANICAL DIMENSIONS



NOTE: ALL DIMENSIONS IN INCHES (mm).

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